

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

PATENT APPLICATION

Inventors: Pooran Chandra Joshi, Apostolos T.
Voutsas, and John W. Hartzell

Attorney Docket No.
SLA0786

Serial No: Not Yet Assigned

Filed: Herewith

Title: HIGH DENSITY PLASMA PROCESS
FOR THE FORMATION OF SILICON
DIOXIDE ON SILICON CARBIDE
SUBSTRATES

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

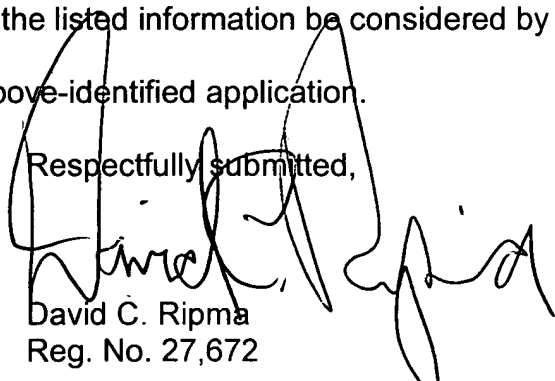
Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

March 29, 2004
(Date)

Respectfully submitted,


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Disclosure SLA0786

FORM PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION				DOCKET NUMBER SLA786		APPLICATION NUMBER	
				APPLICANT Joshi et al.			
				FILING DATE:		GROUP ART UNIT	

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FIL. DATE IF APPROP.
	6,136,727	10/24/00	Ueno	438	770	12/18/98
	6,437,371	8/20/02	Lipkin et al.	257	77	2/12/01
	6,482,704	11/19/02	Amano et al.	438	285	11/17/00

FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO

OTHER DOCUMENTS	
	"Rapid oxidation of SiC using microwave-discharged O ₂ plasma at low temperatures (<300 °C)", M. Satoh, H. Shimada, T. Nakamura, and S. Yanagihara, Japanese Journal of Applied Physics, Vol. 41, pp. L233-L235, 2002.
EXAMINER	DATE CONSIDERED